



Docket No. YOR919990408CIP/YOR129 CIP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Cabral, Jr., et al.

Serial No.: 09/902,483

Group Art Unit: 2813

Filing Date: July 11, 2001

Examiner: Erik J. Kielin

For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY
CONTACTS TO THIN FILM SILICON-ON-INSULATOR AND BULK MOSFETS
AND FOR SHALLOW JUNCTIONS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

PRIOR ART SUBMISSION

Sir:

For the possible benefit of anyone subsequently evaluating the scope and/or validity of the above patent, it is respectfully requested that the following references cited in the corresponding Korean Patent Application, be placed in the file wrapper:

1. Japanese Patent Application No. 11-177103 with abstract

The undersigned has not reviewed the teachings of these references in detail and thus makes no representations concerning their relevancy or materiality.

Respectfully submitted,

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Date: 11/15/04

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